

## P-Channel Enhancement Mode Power MOSFET

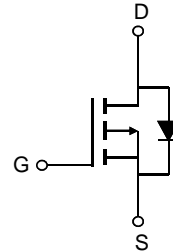
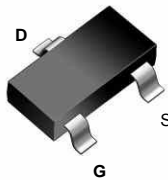
### General Description

The DMG3130LQ uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

### Features

$V_{DS}$	-30V
$I_D$ (at $V_{GS}=-10V$ )	-5.0A
$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	50m $\Omega$ (Max)
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	65m $\Omega$ (Max)
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$ )	90m $\Omega$ (Max)

**SOT23**



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	$V_{DS}$	-30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V	
Drain Current-Continuous	TC=25 $^\circ\text{C}$	$I_D$	-5.0	A
	TC=100 $^\circ\text{C}$	$I_D$	-3.5	A
Drain Current – Pulsed	$I_{DM}$	-20	A	
Maximum Power Dissipation	$P_D$	2.1	W	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$	

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance junction-case	$R_{\theta Jc}$		1.1	$^\circ\text{C}/\text{W}$
Thermal Resistance junction-to-Ambient	$R_{\theta JA}$		60	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.5	-0.9	-1.5	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.0A		41	50	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A		50	65	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A		60	90	mΩ
<b>DYNAMIC PARAMETERS</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz		640		pF
C <sub>OSS</sub>	Output Capacitance			80		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			55		pF
<b>SWITCHING PARAMETERS</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =-15V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω		6.5		nS
t <sub>r</sub>	Turn-on Rise Time			3.5		nS
t <sub>d(off)</sub>	Turn-Off Delay Time			41		nS
t <sub>f</sub>	Turn-Off Fall Time			9		nS
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.0A, V <sub>GS</sub> =-10V		14		nC
Q <sub>gs</sub>	Gate-Source Charge			1.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			1.6		nC
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>SD</sub> =-1A		0.72	1.4	V
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz		7		Ω

**Note:**

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%.
3. Essentially independent of operating temperature.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

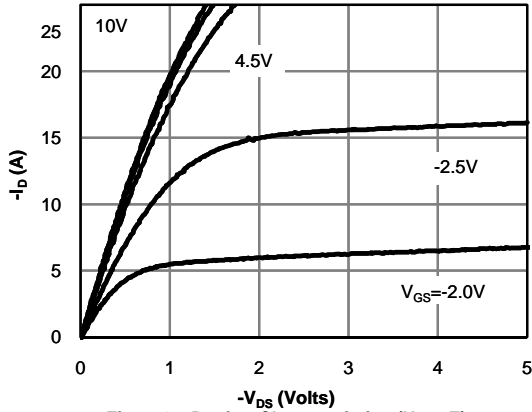


Fig 1: On-Region Characteristics (Note E)

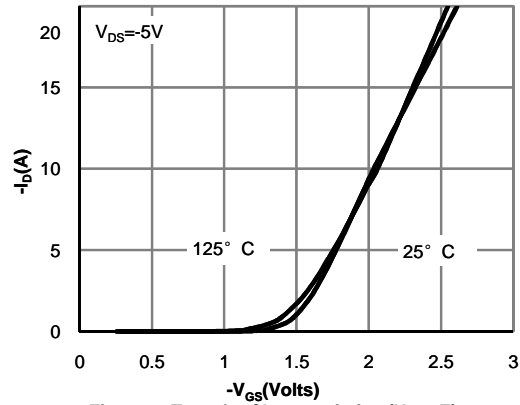


Figure 2: Transfer Characteristics (Note E)

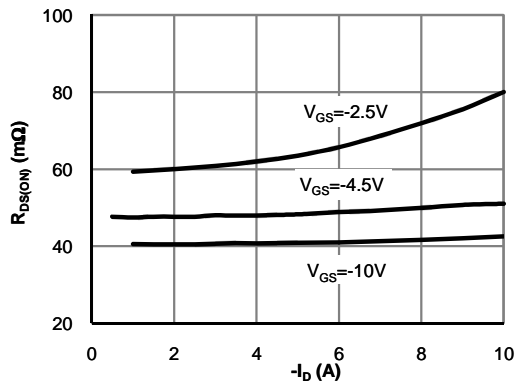


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

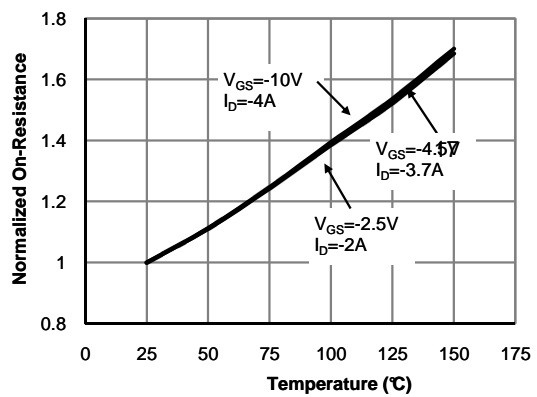


Figure 4: On-Resistance vs. Junction Temperature (Note E)

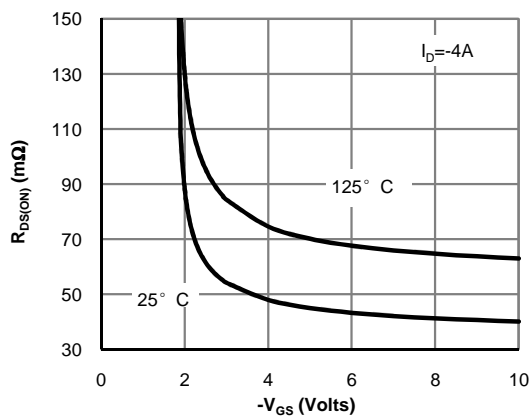


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

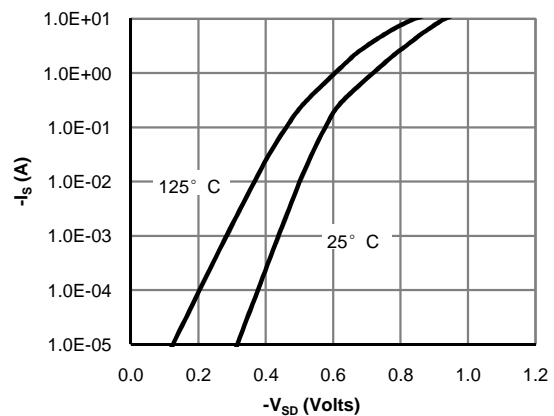


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

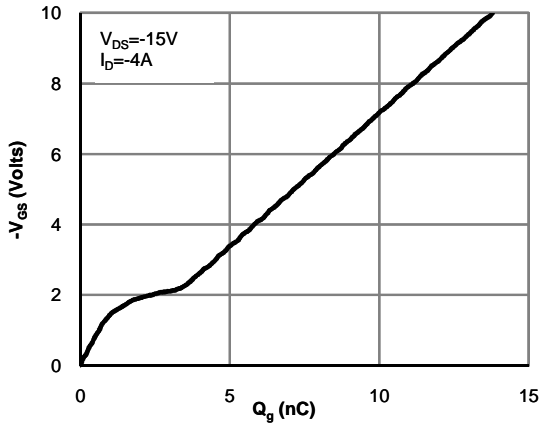


Figure 7: Gate-Charge Characteristics

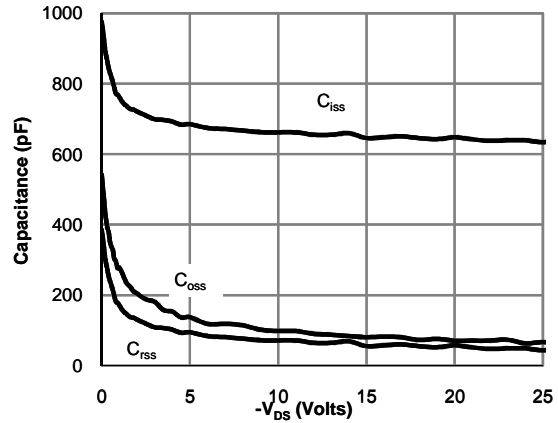


Figure 8: Capacitance Characteristics

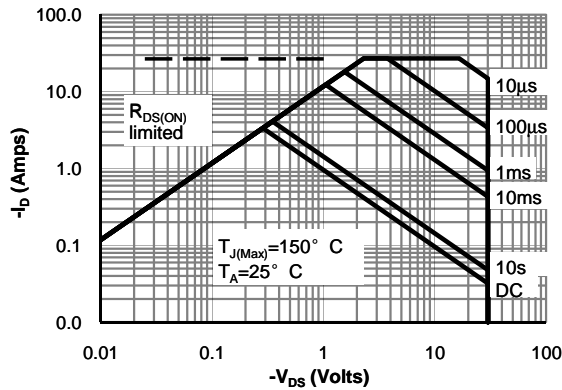


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

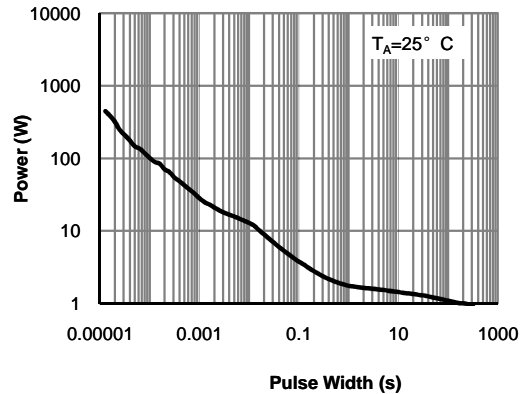


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

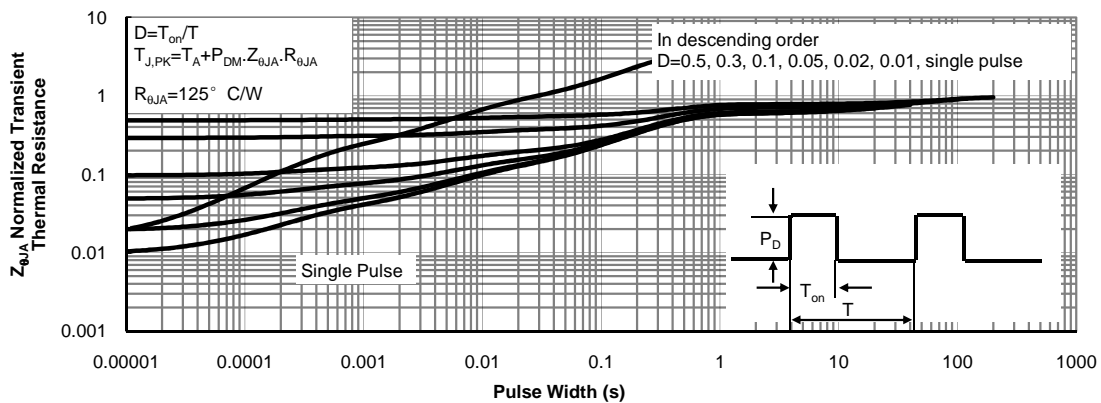
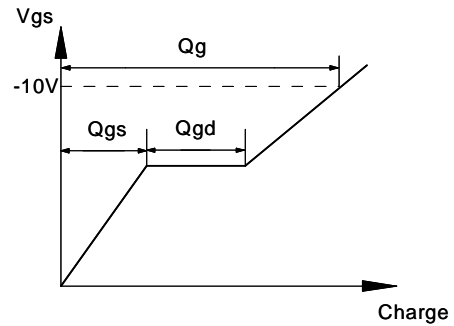
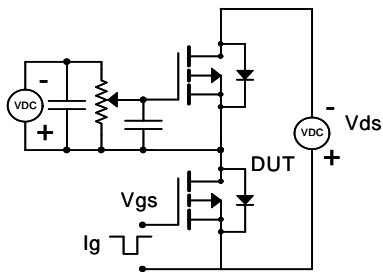
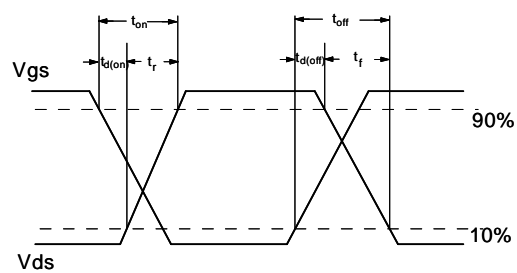
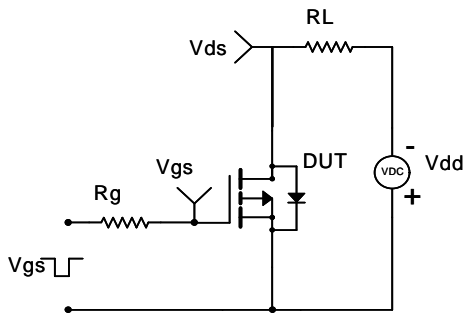


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

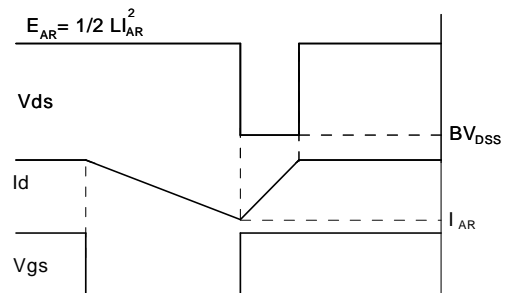
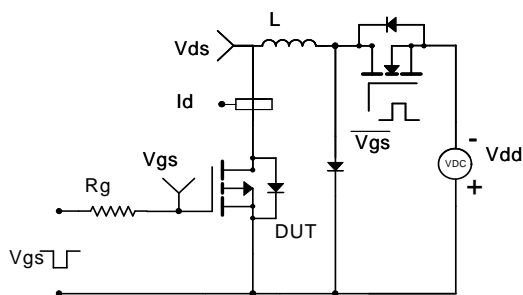
### Gate Charge Test Circuit & Waveform



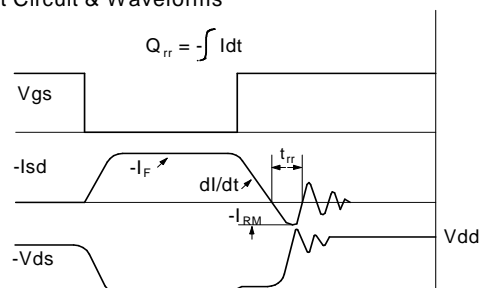
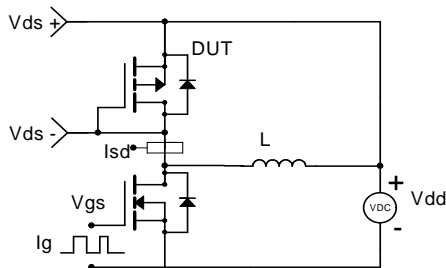
### Resistive Switching Test Circuit & Waveforms



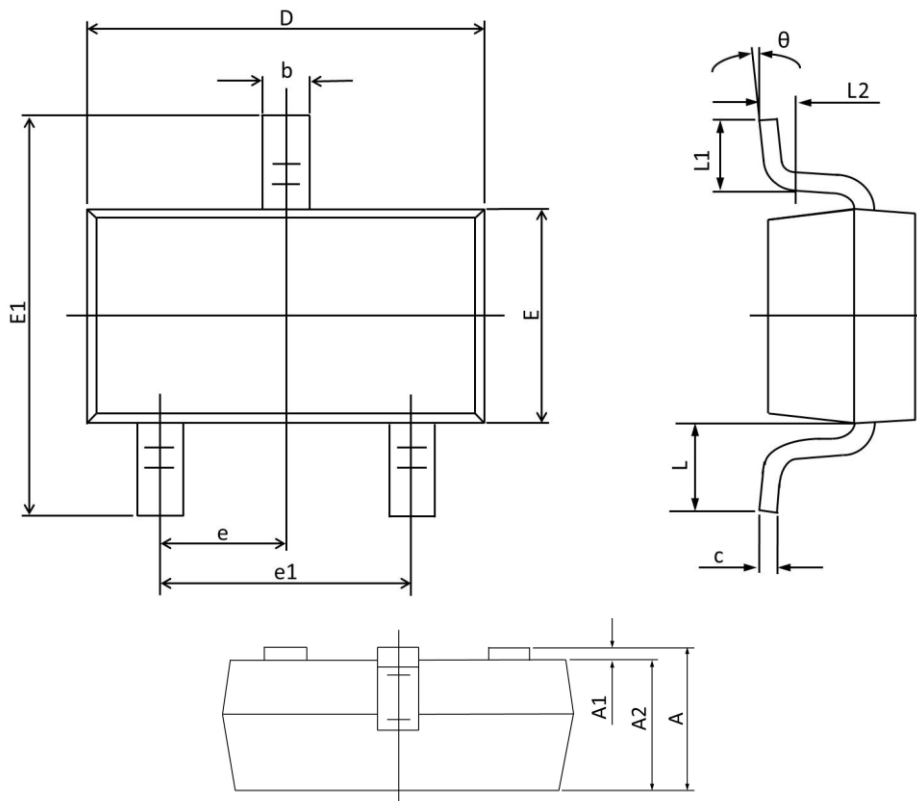
### Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



### Diode Recovery Test Circuit & Waveforms



SOT23 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Max	Min	Max	Min
A	1.150	0.900	0.045	0.035
A1	0.100	0.000	0.004	0.000
A2	1.050	0.900	0.041	0.035
b	0.500	0.300	0.020	0.012
c	0.150	0.080	0.006	0.003
D	3.000	2.800	0.118	0.110
E	1.400	1.200	0.055	0.047
E1	2.550	2.250	0.100	0.089
e	0.95 TYP.		0.037 TYP.	
e1	2.000	1.800	0.079	0.071
L	0.55 REF.		0.022 REF.	
L1	0.500	0.300	0.020	0.012
L2	0.25 TYP.		0.01 TYP.	
$\theta$	8°	0°	8°	0°

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